

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claim 1. (Currently Amended) A ferroelectric liquid crystal display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, a second conductive layer being in contact with said first conductive layer and a ~~second~~ third conductive layer being in contact with said gate insulating film, side surfaces of the first conductive layer and top and side surfaces of said ~~first~~ second conductive layer;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a pair of LDD regions and first source and drain regions; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and second source and drain regions,

wherein said second conductive layer comprises a different material from said first conductive layer;

wherein a portion which said ~~second~~ third conductive layer is in contact with said gate insulating film in said n-channel TFT partially overlaps said pair of LDD regions;

wherein a portion which said ~~second~~ third conductive layer is in contact with said gate insulating film in said p-channel TFT partially overlaps said second source and drain regions,

wherein said semiconductor layer of said p-channel TFT has no LDD regions.

Claim 2. (Previously Presented). A ferroelectric liquid crystal display device according to claim 1, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 3. (Previously Presented). A ferroelectric liquid crystal display device according to claim 1, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises a single layer or a plurality of layers.

Claim 4. (Currently Amended). A ferroelectric liquid crystal display device according to claim 1, wherein said ~~second~~ third conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 5. (Canceled).

Claim 6. (Currently Amended) A ferroelectric liquid crystal display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, a second conductive layer being in contact with said first conductive layer and a ~~second~~ third conductive layer being in contact with said gate insulating film, side surfaces of said first conductive layer and top and side surfaces of said ~~first~~ second conductive layer;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a pair of LDD regions and first source and drain regions; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and second source and drain regions,

wherein said second conductive layer comprises a different material from said first conductive layer;

wherein a portion which said ~~second~~ third conductive layer is in contact with said gate insulating film in said n-channel TFT partially overlaps said pair of LDD regions;

wherein the portion which said ~~second~~ third conductive layer is in contact with said gate insulating film in said n-channel TFT does not overlap said first source and drain regions;

wherein a portion which said ~~second~~ third conductive layer is in contact with said gate insulating film in said p-channel TFT partially overlaps said second source and drain regions,

wherein said semiconductor layer of said p-channel TFT has no LDD regions.

Claim 7. (Previously Presented). A ferroelectric liquid crystal display device according to claim 6, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 8. (Previously Presented). A ferroelectric liquid crystal display device according to claim 6, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises a single layer or a plurality of layers.

Claim 9. (Currently Amended). A ferroelectric liquid crystal display device according to claim 6, wherein said ~~second~~ third conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 10. (Canceled).

Claim 11. (Currently Amended) A ferroelectric liquid crystal display device having an n-channel TFT and a p-channel TFT over a substrate,

said n-channel TFT comprising:

a first gate electrode and a second gate electrode formed adjacent to a first semiconductor layer with a first gate insulating film interposed therebetween, said first semiconductor layer comprising a first channel formation region, a pair of LDD regions and first source and drain regions;

wherein said ~~first~~ second gate electrode partially overlaps said pair of LDD regions while said first gate electrode does not overlap said pair of LDD regions, and

said p-channel TFT comprising:

a ~~second~~ third gate electrode and a fourth gate electrode formed adjacent to a second semiconductor layer with a second gate insulating film interposed therebetween, said second semiconductor layer comprising a second channel formation region and second source and drain regions being in contact with said second channel formation region,

wherein said ~~second~~ fourth gate electrode partially overlaps said second source and drain regions while the third gate electrode does not overlap said second source and drain regions, and

wherein a wiring is connected to at least one of said second source and drain regions.

Claim 12. (Currently Amended). A ferroelectric liquid crystal display device according to claim 11, wherein said first ~~and second~~ to fourth gate electrodes comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 13. (Canceled).

Claim 14. (Currently Amended) A goggle type display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, a second conductive layer being in contact with said first conductive layer, and a ~~second~~ third conductive layer being in contact with said gate insulating film, side surfaces of said first conductive layer and top and side surfaces of said ~~first~~ second conductive layer;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a pair of LDD regions and first source and drain regions; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and second source and drain regions,

wherein said second conductive layer comprises a different material from said first conductive layer;

wherein a portion which said ~~second~~ third conductive layer is in contact with said gate insulating film in said n-channel TFT partially overlaps said pair of LDD regions;

wherein a portion which said ~~second~~ third conductive layer is in contact with said gate insulating film in said p-channel TFT is partially overlaps said second source and drain regions,

wherein said semiconductor layer of said p-channel TFT has no LDD regions.

Claim 15. (Previously Presented). A goggle type display device according to claim 14, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 16. (Previously Presented). A goggle type display device according to claim 14, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises a single layer or a plurality of layers.

Claim 17. (Currently Amended). A goggle type display device according to claim 14, wherein said ~~second~~ third conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 18. (Canceled).

Claim 19. (Currently Amended) A goggle type display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, a second conductive layer being in contact with said first conductive layer, and a ~~second~~ third conductive layer being in contact with said gate insulating film, side surfaces of said first conductive layer and top and side surfaces of said ~~first~~ second conductive layer;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a pair of LDD regions and first source and drain regions; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and second source and drain regions,

wherein said second conductive layer comprises a different material from said first conductive layer;

wherein a portion which said ~~second~~ third conductive layer is in contact with said gate insulating film in said n-channel TFT partially overlaps said pair of LDD regions;

wherein the portion which said ~~second~~ third conductive layer is in contact with said gate insulating film in said n-channel TFT does not overlap said first source and drain regions;

wherein a portion which said ~~second~~ third conductive layer is in contact with said gate insulating film in said p-channel TFT partially overlaps said second source and drain regions,

wherein said semiconductor layer of said p-channel TFT has no LDD regions.

Claim 20. (Previously Presented). A goggle type display device according to claim 19, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 21. (Previously Presented). A goggle type display device according to claim 19, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises a single layer or a plurality of layers.

Claim 22. (Currently Amended). A goggle type display device according to claim 19, wherein said ~~second~~ third conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 23. (Canceled).

Claim 24. (Currently Amended) A goggle type display device having an n-channel TFT and a p-channel TFT over a substrate,

said n-channel TFT comprising:

a first gate electrode and a second gate electrode formed adjacent to a first semiconductor layer with a first gate insulating film interposed therebetween, said first semiconductor layer comprising a first channel formation region, a pair of LDD regions and first source and drain regions;

wherein said ~~first~~ second gate electrode partially overlaps said pair of LDD regions while said first gate electrode does not overlap said pair of LDD regions, and

said p-channel TFT comprising:

a ~~second~~ third gate electrode and fourth gate electrode formed adjacent to a second semiconductor layer with a second gate insulating film interposed therebetween, said second semiconductor layer comprising a second channel formation region and second source and drain regions being in contact with said second channel formation region,

wherein said ~~second~~ fourth gate electrode partially overlaps said second source and drain regions while said third gate electrode does not overlap said second source and drain

regions, and

wherein a wiring is connected to said at least one of said second source and drain regions.

Claim 25. (Currently Amended). A goggle type display device according to claim 24, wherein said first ~~and second~~ to fourth gate electrodes comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 26. (Canceled).